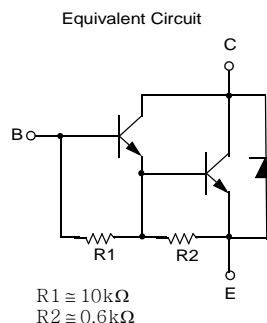
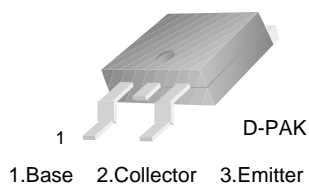


# MJD112

## NPN Silicon Darlington Transistor

### Features

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)



### Absolute Maximum Ratings\* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current (DC)	2	A
$I_{CP}$	Collector Current (Pulse)	4	A
$I_B$	Base Current	50	mA
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	20	W
	Collector Dissipation ( $T_a=25^\circ\text{C}$ )	1.75	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Electrical Characteristics\* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 30\text{mA}, I_B = 0$	100		V
$I_{CEO}$	Collector Cut-off Current	$V_{CE} = 50\text{V}, I_B = 0$		20	$\mu\text{A}$
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 100\text{V}, I_B = 0$		20	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$		2	mA
$h_{FE}$	* DC Current Gain	$V_{CE} = 3\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 3\text{V}, I_C = 2\text{A}$ $V_{CE} = 3\text{V}, I_C = 4\text{A}$	500 1000 200	12K	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 8\text{mA}$		2	V
		$I_C = 4\text{A}, I_B = 40\text{mA}$		3	V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = 4\text{A}, I_B = 40\text{mA}$		4	V
$V_{BE(on)}$	* Base-Emitter On Voltage	$V_{CE} = 3\text{A}, I_C = 2\text{A}$		2.8	V
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.75\text{A}$	25		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0$ $f = 0.1\text{MHz}$		100	pF

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

# Typical Characteristics

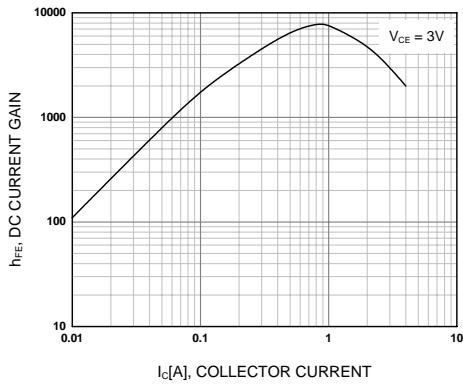


Figure 1. DC current Gain

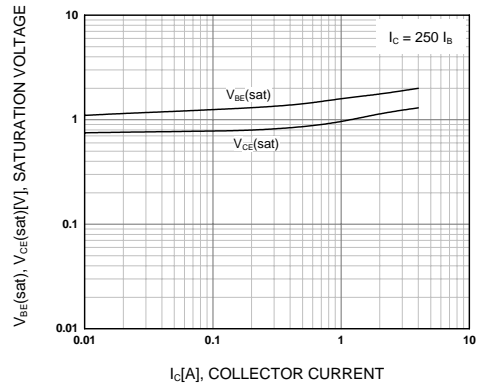


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emmitter Saturation Voltage

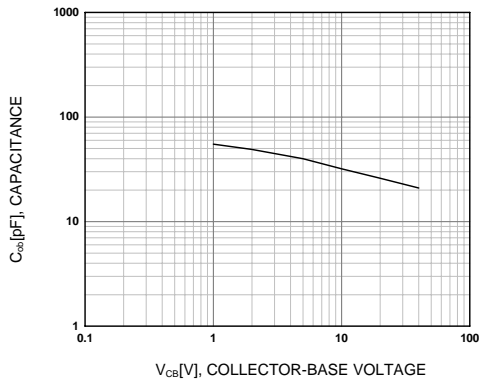


Figure 3. Collector Output Capacitance

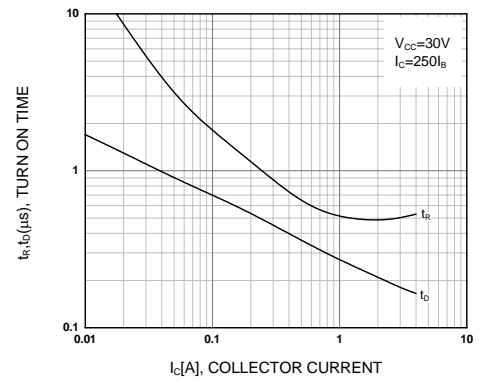


Figure 4. Turn On Time

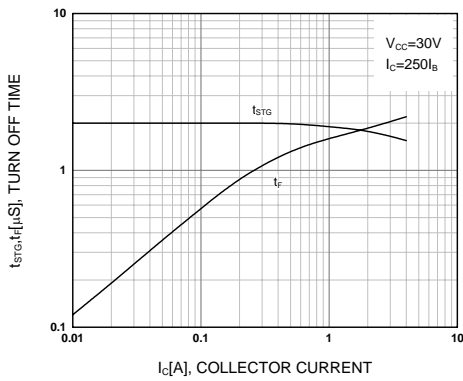


Figure 5. Turn Off Time

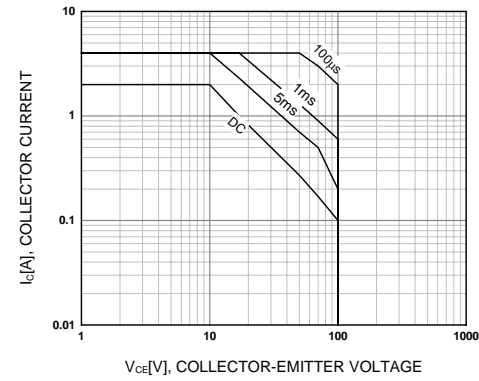


Figure 6. Safe Operating Area

### Typical Characteristics (Continued)

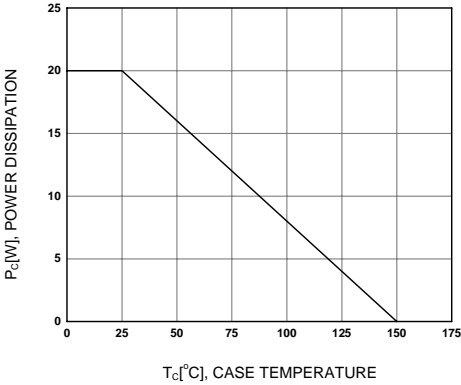


Figure 1. Power Derating



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EnSigna™	LittleFET™	PowerTrench®	TCM™	
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FAST®	MicroFET™	QS™	TinyBuck™	
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Programmable Active Droop™				

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